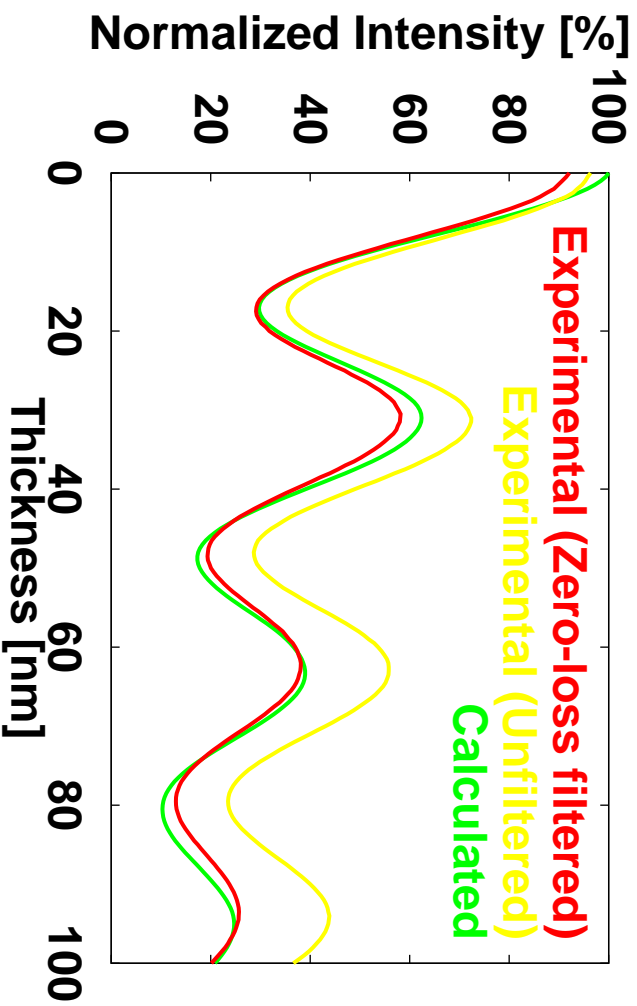
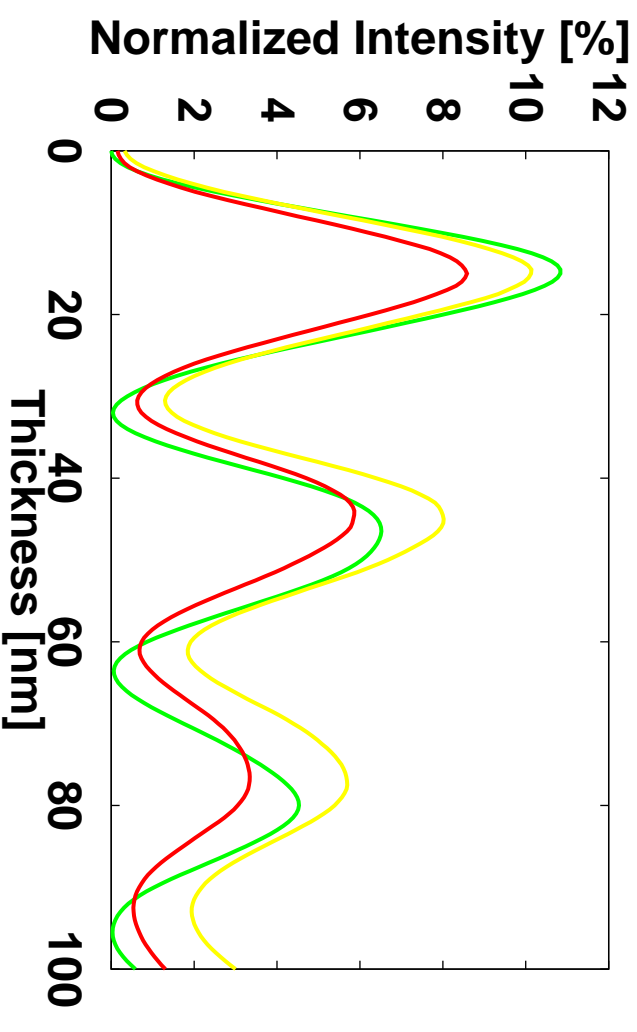


—Si—

a 000 ($r = 0.998$)



b 022 ($r = 0.964$)



c 040 ($r = 0.958$)

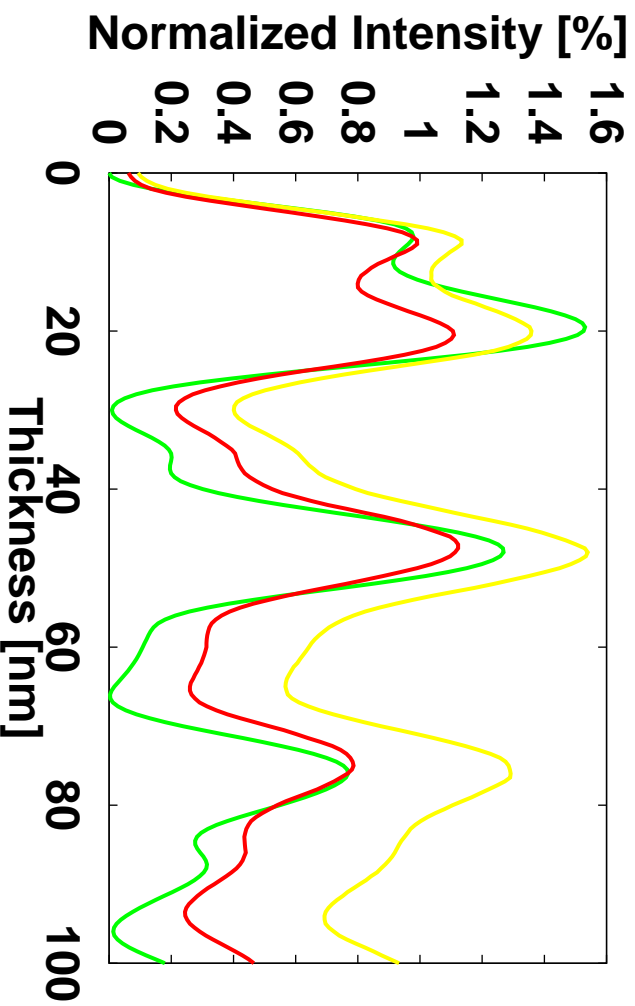
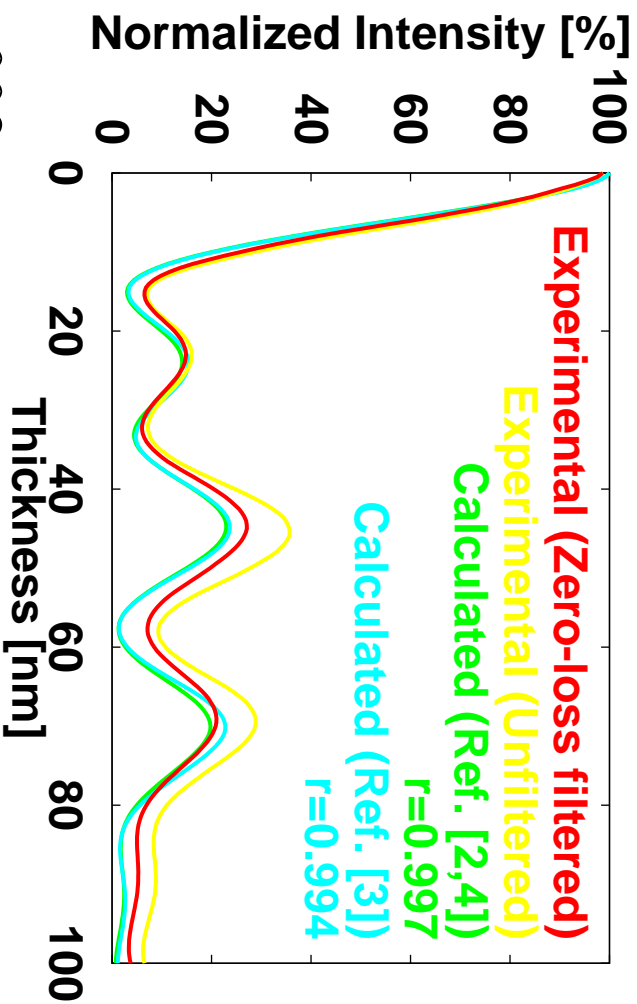


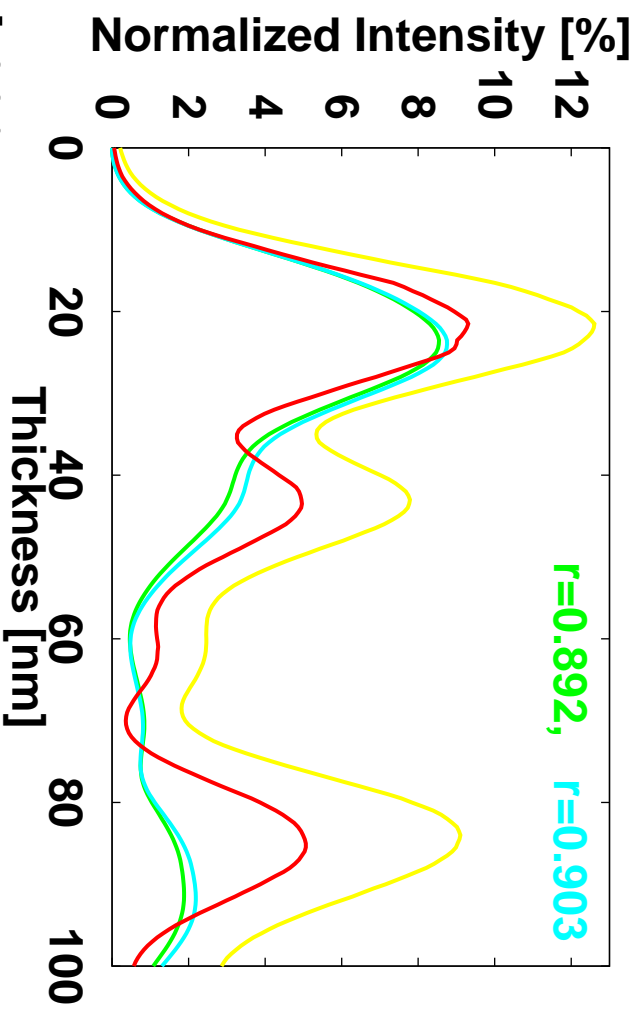
Fig. 1 Dependence of diffraction intensity on crystal thickness for [100] Si crystal axially illuminated by a 200 keV electron beam. Zero-loss filtered (**red**) and unfiltered (**yellow**) intensity profiles, and calculated intensity profiles (**green**) at $B = 0.45 \text{ \AA}^2$ and $\gamma = 4\%$. The correlation coefficients, r , between the zero-loss filtered and the calculated ones are indicated.

— MgO —

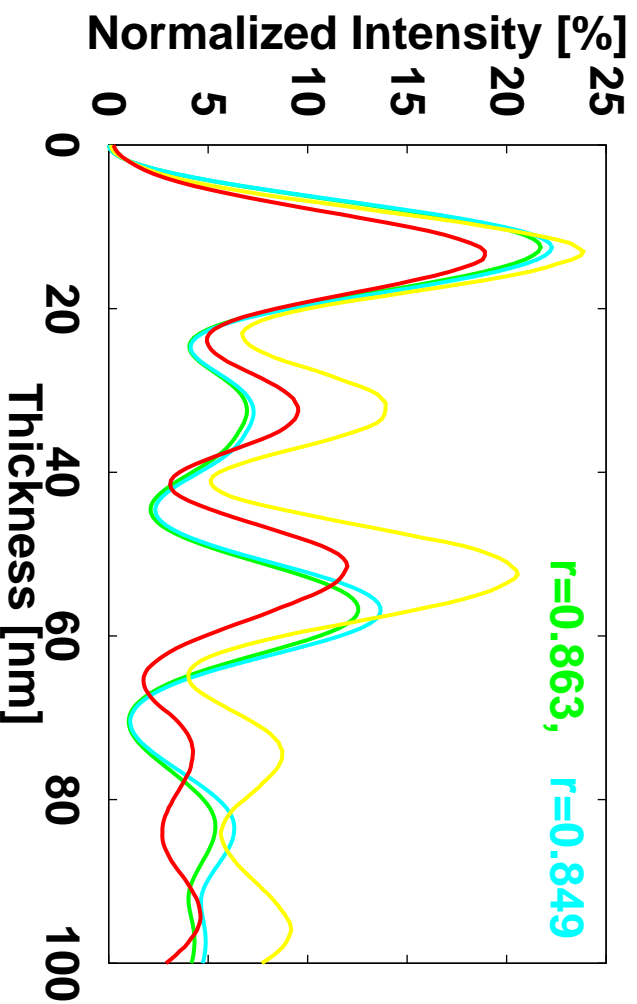
a 000



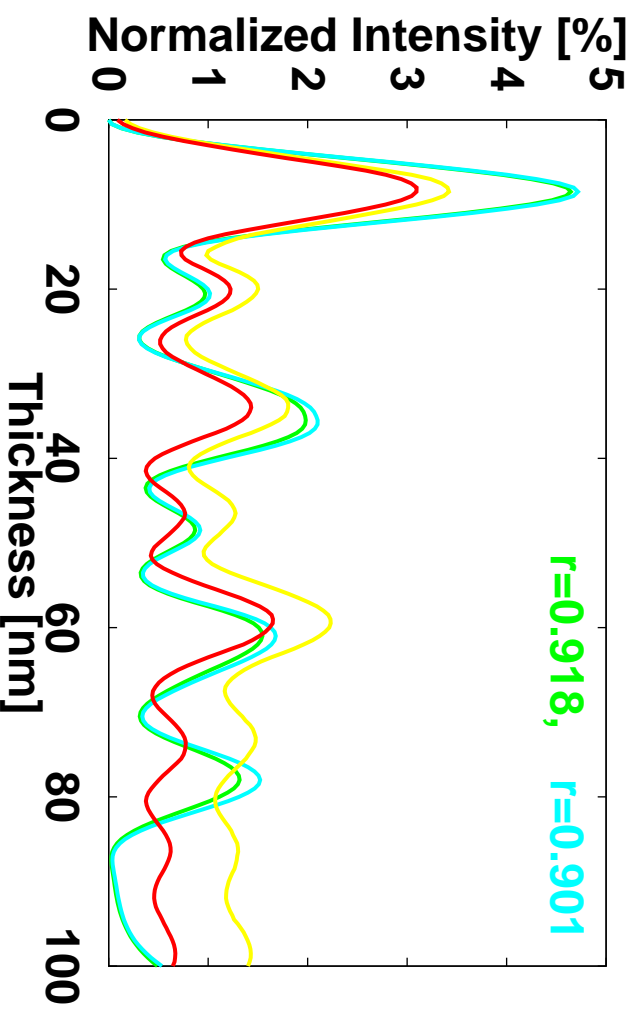
b 111



c 002



d 220



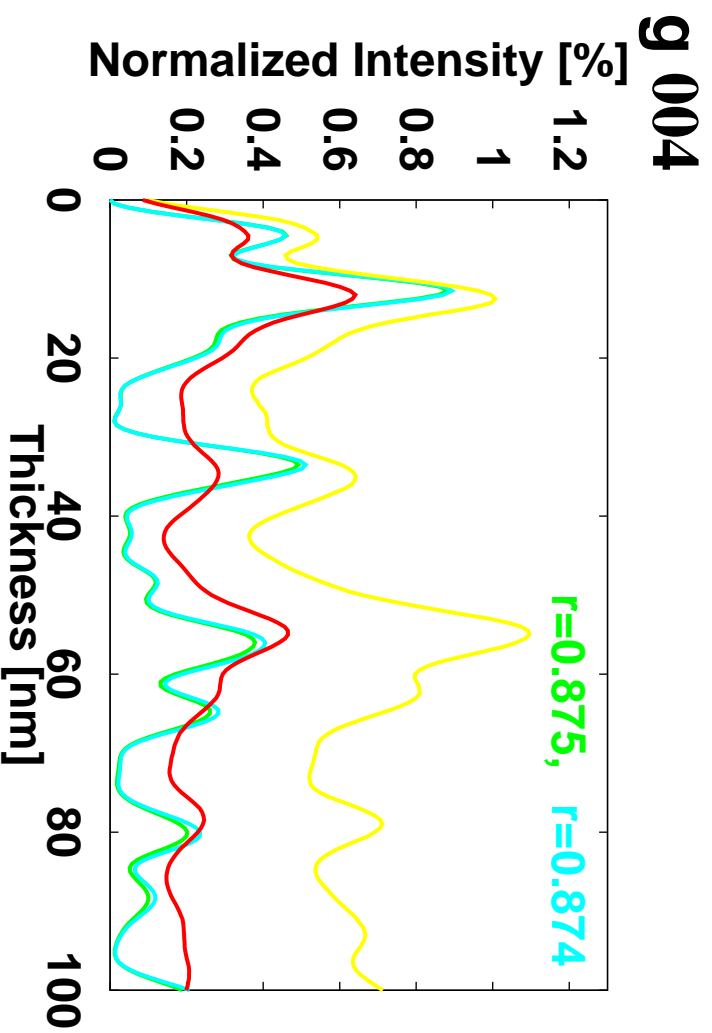
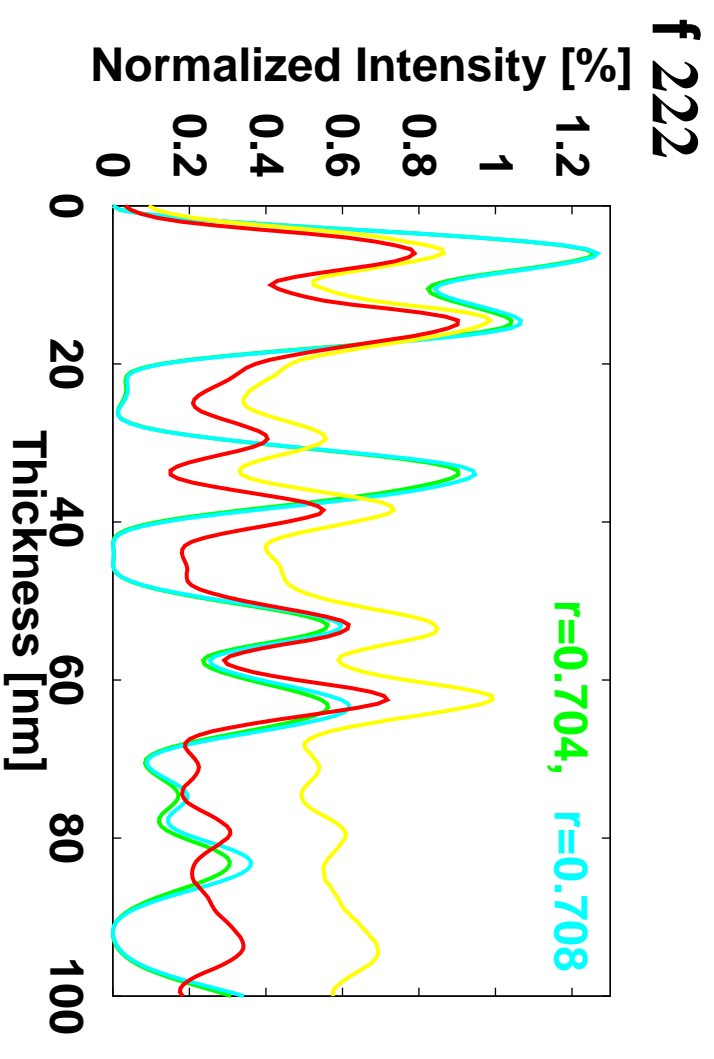
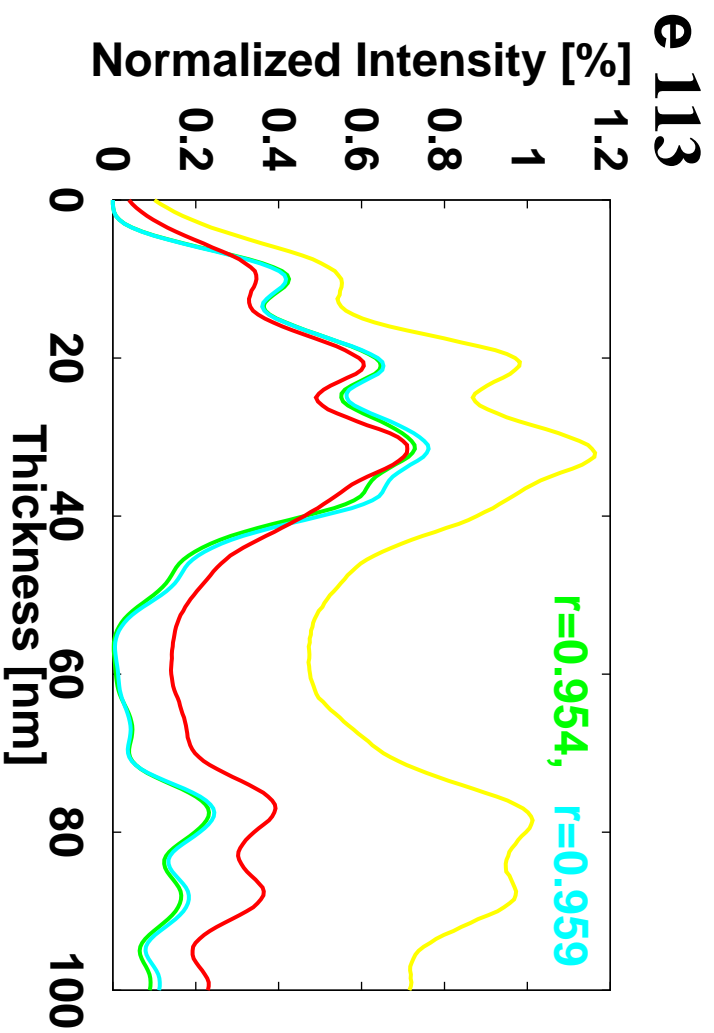


Fig. 3 Dependence of diffraction intensity on crystal thickness for [1 $\bar{1}$ 0] MgO crystal axially illuminated by a 200 keV electron beam. Zero-loss filtered (**red**) and unfiltered (**yellow**) intensity profiles, and calculated intensity profiles (**green**, **blue**) best matching with the zero-loss filtered ones (see below). The correlation coefficients, r , are also indicated.

	f_{ion}	γ	x
Green	Ref. [2,4]	4 %	65 %
Blue	Ref. [3]	4 %	100 %

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